Theory of dopants and defects in Co-doped T iO $_2$ anatase

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We report rst-principles m icroscopic calculations of the form ation energy, electrical activity, and m agnetic m om ent of C o dopants and a variety of native defects in T iO₂ anatase. U sing these results, we use equilibrium therm odynam ics to predict the resulting carrier concentration, the average m agnetic m om ent per C o, and the dom inant oxidation state of C o. The predicted values are in good agreem ent with experim ent under the assumption of O poor growth conditions. In this regime, a substantial fraction of C o dopants occupy interstitial sites as donors. The incom plete com pensation of these donors by substitutional C o acceptors then leads to n-type behavior, as observed experim entally.

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I. IN TRODUCTION

The recent discovery of room tem perature ferrom agnetism in Co-doped TiO₂ anastase¹ has led to a great deal of activity both to understand the origins of ferrom agnetic order in this material and to raise the magnetic ordering tem perature^{2,3,4,5,6,7,8,9} One prom ising line of inquiry is to understand st the role of dopants and native defects in the T iO 2 host. For exam ple, the location of Co dopants in this material (substitutional versus interstitial), their oxidation state, and their magnetic properties have been the subject of intense scrutiny.^{2,3,4,6,8} Furthermore, it has been suggested that O vacancies, which are believed to give rise to the observed n-type behavior in pure T iO $_2$ anatase,¹⁰ m ay provide free electrons which mediate the exchange interaction between the Co dopants.^{3,4} This possibility is very di erent from the hole mediated exchange interactions which are believed to describe ferrom agnetic order in a wide variety of other dilute m agnetic sem iconductors, including InM nAs, GaM nAs, and M nG $e_{t}^{11,12,13}$ and m ay have a direct bearing on the origin of the anom alously high C urie tem perature observed in Co-doped T iO $_2$ anatase.

In this paper, we rst use density-functional theory to determ ine the electronic structure, form ation energy, and electrical activity of C o dopants and several native defects in T iD₂ anatase. (In the remainder of this paper we will use \defects" to refer to both C o dopants and native defects.) We then use standard methods to calculate, as a function of temperature, the concentrations of each defect in the T iD₂ host over a range of C o and O chemical potentials relevant to di erent grow th conditions. In summary, we nd that O vacancies do not play any signi cant role in C o-doped anatase. Moreover, we

nd that the observed n-type behavior in Co-doped T iD_2 strongly suggests that roughly half of the total Co content is in interstitial sites. Under these conditions we nd an enhancement relative to the Co²⁺ low spin state of the average value of the local magnetic moment, in good agreement with experiment. Finally, under these conditions essentially all of the of Co both interstitial and substitutional occurs in oxidation state II, as observed

experim entally.

II. BACKGROUND

We begin by brie y reviewing the relevant experimental results for Co-doped T iO₂ anatase. We concentrate solely on experimental results for samples in which Co is believed to be hom ogeneously distributed; hence, we do not address Co clustering or its consequences. We focus on three observations which show good experimental reproducibility: (1) the electrical nature of the samples (insulating versus n-type or p-type), (2) the Co oxidation state, and (3) the average magnetic moment per Co dopant.

A though the original work of M atsum oto and cow orkers estim ated the ferrom agnetic ordering tem perature to be larger than 400 K, the average magnetic moment per Co and n-type carrier concentration were modest, 0.32 _B and 10^{18} /cm³ respectively. More recent e orts have led to a larger magnetic moment per Co of 126 $_{\rm B}$ $_{\prime}^{2,3,4}$ and to n-type carrier densities of 10¹⁹/cm³.¹⁴ These increased values are likely due to improvements in sam ple quality achievable with oxygen plasm a-assisted molecular-beam epitaxy (OPMBE).¹⁵ Forexample, these samples were well characterized to rule out Co inclusions as a source of the ferrom agnetism .4,14 U sing both Co 2p photoem ission and Co K-shell x-ray absorption near-edge structure (XANES), the Co dopants in TiO_2 anatase were shown to have a form aloxidation state of II.A strong correlation between the magnetic and transport properties was dem onstrated: both highly doped and highly resistive sam ples are typically non-m agnetic, consistent with a picture of carrier-m ediated ferrom agnetism competing with an antiferrom agnetic superexchange interaction.4,14

III. THEORY

A. Form alism

To understand the role of defects in T iO₂ anatase, we initially adopt a simple picture of isolated in purities. In this approach, we rst determ ine the energy required for the defect to form in a given charge state. We then use a standard therm odynam ic approach to determ ine the expected concentration of such defects at a given temperature. We assume that the defects do not interact, except indirectly via charge transfer between them. Thus, for example, we do not address the origin of the apparent ferrorm agnetic coupling between C o dopants.

The defects we consider in this work are: interstitial Co (Co_{int}), substitutionalCo on the Tisite (Co_Ti), O vacancies (V₀), interstitialTi (Ti_{int}), and defect com plexes consisting of nearest-neighbor pairs of substitutionalCo and O vacancies (Co_TiV₀). There are two crystallographically distinct types of such com plexes: a Co_TiV₀ pair oriented along the c-axis and a Co_TiV₀ pair oriented nearly in the ab plane. We refer to these as Co_TiV₀ -c and Co_TiV₀ -ab, respectively.

We make no assumptions about which defects are donors and which are acceptors, whether they are neutral or charged, or how many are actually present. At a given temperature, the concentration of each defect (in a given charge state) will be determined by its form ation energy. We use density-functional theory in a supercell approach to calculate these form ation energies according to

$$E_{form}^{q} = E_{t}^{q} \qquad \begin{array}{c} X \\ n_{j \ j} + q E_{F}; \end{array}$$
(1)

where E_t^q is the total energy of a supercell containing one defect in charge state q; n_j and j are the number and chem ical potential (energy per atom in the ground-state phase) of each atom ic species in the supercell; and E_F is the Ferm i energy, measured with respect to the valence band maximum (VBM) of the host.^{16,17,18,19,20} A though the Ferm i energy appears to be an independent variable here, it is in fact determined by the constraint of electroneutrality, as described below. A lso, we note that although the total energies on the right-hand side of Eq. 1 depend on whether all-electron or pseudopotentialm ethods are used, the form ation energy itself is analogous to a binding energy, and can therefore be accurately calculated within either m ethod.

In them al equilibrium, the concentration of each defect, D, is determ ined by its form ation energy:

$$C_{D}^{q} = N_{sites} \exp \left(E_{form}^{q} = k_{B} T \right);$$
 (2)

where N _{sites} is the number of sites per unit volum e available to the defect. Since the form ation energies depend on the chem ical potentials and the Ferm i level, it is evident that the concentrations also depend on these quantities. The concentrations must also satisfy the constraint of overall electrical neutrality; this provides an additional equation that we use to determ ine E_F for any given choice of chem ical potentials. The electroneutrality condition m ust take into account the contributions not only from charged defects, but also from p and n (the hole and electron carrier densities). Thus, for each given choice of the oxygen chem ical potential, $_{\circ}$, and cobalt chem ical potential, $_{co}$, the following equation m ust be num erically solved:

$$p(E_{\rm F})$$
 $n(E_{\rm F}) + \int_{D_{\rm F}q}^{X} qC_{\rm D}^{\rm q} (E_{\rm F}; o; c_{\rm o}) = 0:$ (3)

Here, the sum is over all defects, D, in all possible charge states, q. The T i chem ical potential does not enter explicitly into this equation for reasons discussed in the following section, and, of course, the C o chem ical potential is only relevant for defects involving C o. The carrier densities p and n are evaluated using the conventional sem iconductor expressions along with the ab initio density of states of the host m aterial, with a scissors operator applied to give the experimental band gap.

B. Chem ical Potentials

The atom ic chem ical potentials, $_{j}$, on the right hand side of Eq. 1 are closely related to the experimental growth conditions. A high value of chem ical potential of a particular atom ic species is equivalent to a growth environment that is rich in that species (in the sense of high partial pressure).

The chem ical potentials of T i and O which enter into Eq.1 are not independent: equilibrium between the T i and O atom ic reservoirs and bulk T iD $_2$ anatase requires that

$$T_{1} + O_{2} = T_{1}O_{2};$$
 (4)

where $_{TiO_2}$ is the total energy of bulk anatase. Moreover, in order to preclude the precipitation of bulk hcp $TiorO_2$ dimers there are additional therm odynamic restrictions on the individual chemical potentials:

$$\circ < \circ ;$$
 (5)

and

$$T_{i} < {}^{\text{bulk}}_{T_{i}};$$
 (6)

where $^{\circ}_{0}$ is the energy per atom in an O₂ dimer in its spin triplet ground state and $^{bu\,lk}_{T\,i}$ is the energy per atom in hcp T i. It is conventional to refer to the upper lim it in Eq. 5 as the O-rich lim it and, sim ilarly, to the upper lim it in Eq. 6 as the T i-rich lim it. Because of the relationship between Ti and o in Eq. 4, there are only two independent variables in this approach: the O and Co chem ical potentials. This explains why the T i chem ical potential does not enter explicitly into Eq. 3. Thus, for a given choice of $_{Co}$ and $_{O}$, all the other quantities (including E_F) in Eq.3 are completely determined. In practice, we eliminate $_{Co}$ as an independent variable by constraining the total Co concentration to a typical experimental value (5%). Hence, in our formulation, the concentration of all defects is entirely determined by the choice of O chemical potential and the constraint of total Co concentration.

C. Tem perature

A lthough tem perature appears in both Eq.1 (in plicitly) and Eq.2 (explicitly), our results are not especially sensitive to this variable. Moreover, we stress that the tem perature appearing in Eq.2 has no connection to the magnetic ordering tem perature, and should instead be understood simply as the tem perature at which we evaluate the concentration of defects in equilibrium with their respective reservoirs. Upon completion of growth, we consider the reservoirs to be disconnected and hence the number of these constituents to be xed. Thus we set the tem perature to a particular value and exam ine the behavior of the system as a function of the 0 chem ical potential. To this end, we calculate the defect concentrations using a typical grow th tem perature of 873 K $1^{1,2,7}$

D. Computational D etails

The total energy calculations were performed in a supercell consisting of a 3 3 2 periodic repetition of the prim it ive unit cell; thus, for the pure T iO $_2$ host, these supercells contain 108 atom s. Structural relaxation was performed within a sphere of radius of 4 A centered on the defect in question; calculations using a sphere radius of 5 A give the same total energy to within 50 m eV. This approach has proven both e cient and accurate for other sim ilar m etal-oxide insulators.¹⁹ The total energy calculations were evaluated in the local-density approxim ation (LDA) within the ultrasoft pseudopotential form alism 21 as implemented in the VASP $\operatorname{code}_{r}^{22}$ with the zone center used to sample the Brillouin zone of the supercells. A kinetic-energy cuto of 400 eV was used in all total energy evaluations. Only defects involving Co atom swere treated in a spin-polarized fashion. The ground state of bulk hop Tiwas treated non-magnetically, bulk hop Co was treated in an ferrom agnetic con guration, and the total energy of the O₂ reference dim er was evaluated for the spin triplet.

Since the Ferm i energy in Eq.1 is measured with respect to the VBM of the host, we must align the VBM in the charged defect supercell with that of the host m aterial. To this end, we used a local site average of the electrostatic potential to de ne a reference energy; this local average was evaluated by a test charge approach in which we calculate the electrostatic energy of a narrow G aussian charge distribution far from the defect. W e have checked that using, as an alternative, the T i3p sem icore eigenvalues gives very sim ilar results. Including the zone sampling, kinetic-energy cuto , lattice relaxation and choice of reference energy, we estimate the numerical uncertainty in our results to be 100{150 m eV, su cient for addressing trends with respect to grow th conditions.

To com pute the total energy of a charged periodic system, we use a standard procedure which system atically corrects for the articial and slow ly converging C oulom b interaction between charged defects.^{23,24} A neutralizing hom ogeneous background charge density is rst added to the total charge density; this makes the total energy a well-de ned quantity. Next, the articial interaction am ong the charged defects within this neutralizing background is subtracted from the total energy; this interaction is estim ated by expanding the defect-induced electron density in a multipole series up to quadrupole order and then com puting the contribution to the total energy from the interaction of these multipoles.²⁵

F inally, we note that although the electronic band gap does not enter explicitly into Eq. 1, the LDA underestim ation of the gap does a ect the form ation energies of shallow donors, such as 0 vacancies and interstitial Co.W e have observed, how ever, that the depths of these donor levels (relative to the conduction-band edge) are essentially independent of the value of the band gap. W e dem onstrated this by calculating the position of the donor level using an arti cially reduced lattice constant; as the band gap increases with decreasing lattice constant, the donor level closely tracks the conduction-band edge. Thus, we have corrected the form ation energies of these donors using the experimental value of the band gap and the depth of the donor levels given within LDA. In addition, we assume that the LDA correctly predicts the form ation energies of the +2 charge states of these defects, because all defect levels are empty in this charge state.

IV. RESULTS AND DISCUSSION

A. Electronic Structure of Cori

W e discuss rst the electronic structure of the isolated substitutional C o dopant. Fig. 1 (a) shows the singleparticle levels of neutral substitutional C o, as determ ined from the eigenvalue spectra at k = using a 108-atom supercell. The point group for this defect is D _{2d}, so that all but one of the 3d-orbital degeneracies are lifted by the crystal eld; nevertheless, the environment surrounding the C o dopant is still very nearly cubic, so that the e_g and t_{2g} parentage of these levels is easily seen. There are 3 occupied m a prity-spin levels and 2 occupied m inority-spin levels, yielding a net m agnetic m om ent of 1 _B.

It is instructive to study separately the exchange splitting and crystal- eld splitting. This separation occurs naturally in the q = 1 charge state, for which the exchange splitting vanishes, as shown in Fig. 1 (b). In this case the largest crystal- eld splitting, about 1 eV, is between the e_g and t_{2g} manifolds, with the e_g manifold near the LDA conduction-band edge and the t_{2g} near the valence-band edge. The D $_{2d}$ crystal eld further splits the e_g manifold into an upper a_1 level of z^2 symmetry and a lower b_1 level of $x^2 \;\;y^2$ symmetry; this splitting is 0.3 eV. Likew ise, the crystal eld splits the t_{2g} manifold into an upper b_2 level of xy symmetry and a two-fold e level of (xz, yz) symmetry; this splitting is 0.2 eV.

For charge states with non-zero m agnetic m om ents, we nd that the exchange splitting varies approxim ately linearly with the magnetic m om ent. (Since the orbital m om ent is strongly quenched,²⁶ we regard the magnetic and spin m om ents as equivalent.) For neutral substitutional C o, the exchange splitting within the t_{2g} manifold is 0.2 eV for both levels. Within the t_{2g} manifold, the exchange splitting is strongly orbital-dependent: 0.5 eV for the b_2 levels and 0.3 eV for the e levels.

The calculated m agnetic m om ents of substitutionalC o in di erent charge states, sum m arized in Table I, can now be easily understood from the results of Fig. 1. For the neutral substitutional, there is a two-fold degenerate half-

led m inority spin level at the Ferm i level. R em oving an electron from this level leads to a + 1 charge state with a m om ent of 2 $_{\rm B}$. Likewise, adding an electron to this level leads to a 1 charge state with zero m om ent, since the t_{2g} m anifold is now com pletely led.

The stable charge states and m agnetic m om ents for interstitial C o are quite di erent from the substitutional case. For example, we nd that all charge states experience o -center structural relaxations of order 1A, lifting all rem aining orbital degeneracies. The +2 charge state of interstitial C o, which is the low est-energy charge state over m ost of the gap, has a m om ent of 1 $_{\rm B}$. The +1 charge state leads to a m om ent of 2 $_{\rm B}$, whereas the neutral con quration has a m om ent of 1 $_{\rm B}$.

B. Oxidation State

Since the correspondence between \form all oxidation state" and \charge state" will be an important issue here, we brie y summarize the relationship between the two. A similar discussion has been given for transition-m etal in purities in GaP.¹⁶ W hen a neutral Co substitutes for T in T iO 2, it takes on the oxidation state IV, the same as that of Ti. Hence a substitutional Cori in the 1 charge state has a form al oxidation state of III, and a substitutional Co_{Ti} with charge 2 has an oxidation state of II. In a sim ilar fashion one can relate the oxidation state and charge state of interstitial Co; in this case how ever, the charge state of the dopant is the same as the oxidation state. Hence, neutral interstitial C o has oxidation state 0, the charge state + 1 has oxidation state I, and so forth. The oxidation state of Co-related dopants in their various stable charge states are sum marized in Table I.



FIG.1: First-principles energy-level diagram for substitutional Co_{Ti} in TiO₂ anatase. (a) Neutral charge state; (b) Singly charged state, q = 1. The density of states of the anatase host is shown as the gray shaded regions with a scissors operator applied to give the experim ental band gap. The length of each in purity level is proportional to its d character. The exchange splitting, $_X$, and crystal eld splitting, $_{CF}$, are discussed in Sec. 4 (c) (see text).

TABLE I: Stable charge states of various C o dopants in T iD $_2$ anatase, with their form al oxidation states and calculated m agnetic m om ents. The results for the -2 charge state of C $\sigma_{T\,\,i}$ are obtained from a model described in the text. The oxidation state values in parentheses for C $\sigma_{T\,\,i}V_0$ com plexes are based on the assumption that the neutral com plex can be represented as C $\sigma_{T\,\,i}$ and V $_0$ in the -2 and +2 charge states, respectively.

D efect	Charge C)xidation stat	еМ (_в)
C O _{T i}	1	V	2.0
	0	IV	1.0
	1	III	0.0
	2	II	1.0
Co_{int}	2	II	1.0
	1	I	2.0
	0	0	1.0
$C o_{T i} V_{0} - c$	1	{	2.0
	0	(II)	1.0
$C o_{T i} V_{0}$ -ab	1	{	0.0
	0	(II)	1.0

C. The 2 Charge State of CoTi

In the LDA calculation there is no stable 2 charge state of substitutional Co: upon adding an additional electron to the stable 1 charge state, we nd no dopantderived level within the gap, but rather partial occupation of the LDA conduction bands. This is problem atic, since the experimental nding of an oxidation state of II for Co would be consistent with a 2 charge state for substitutional Co. Here we investigate whether the absence of a 2 charge state within LDA is due to the well-known underestimation of the band gap by the LDA (the LDA predicts a band gap of 2.2 eV compared to the experimental value of 3.2 eV^{27}).

R ather than attem pting to correct the LDA band gap, we propose a more direct description and try to estimate the form ation energy of the 2 charge state using our results for the energy levels of the 1 charge state. Since the formation energy is in general a linear function of the Ferm i energy, we do this in term s of the \energy of transition," E (=), which is de ned as that value of E_F for which $E_{form}^{q=1}$ is equal to $E_{form}^{q=2}$. Referring to Fig. 1(b), we model the 2 charge state by occupying the rst available in purity level in the q = 1 level diagram , namely the empty \boldsymbol{b}_l level. In this diagram , the b_1 level is at $E_F + C_F$, so that occupying it will shift the Ferm i level upw and by an amount $_{CF}$. How ever, by singly occupying this level, one expects an accompanying exchange splitting and thus a downward shift of the Ferm i level. Hence, we estim ate the change in the Ferm i energy between the 1 and 2 charge state to be given by

$$E(=) = E(0=) + _{CF} _{X};$$
 (7)

where E (0=) is the energy of transition between the neutral and 1 charge states; $_{C\,F}$ is the crystal- eld splitting between the b_2 and b_1 levels; and $_X$ is the exchange splitting due to the unpaired b_1 electron.

We approximate $_X$ by the b_1 exchange splitting for the neutral state; this is 0.3 eV, as shown in Fig.1 (a). We neglect the onsite energy which arises from the interaction of the added b_1 electron with the t_{2g} electrons, but we expect this energy to be signicantly smaller than the crystal- eld energy, and hence expect Eq.7 to be reasonably accurate.

A similar proposal could be made for more-negative charge states, for example, the 3 charge state of substitutional C o. However, we should then include an additional term, U, for the onsite interaction between two b_1 electrons of opposite spin. This onsite energy will be large and can be estimated as

$$U = (0=) = (+=0) _{X};$$
 (8)

where $_{\rm X} = 0.3 \, {\rm eV}$ is again taken from the neutral conguration, but in this case accounts for the exchange energy lost when the moment is reduced from 1 $_{\rm B}$ to zero in the transition from the neutral to the 1 charge state.²⁸ We nd U 1.0 eV and, hence, the

3 charge state of substitutional C o will lie well above the conduction-band edge, so that it (and m ore highly charged negative states) can be excluded from further consideration.



FIG. 2: Form ation energies of (a) Co_{Ti} , (b) Co_{int} , (c) $Co_{Ti}V_{\circ}$, (d) V_{\circ} defects as a function of Ferm i level in the O-rich lim it. The Co chem ical potential was chosen to give a total Co concentration of 5%. The Ferm i energy which satis es electroneutrality for these choice of growth conditions and Co concentration is denoted by the dotted vertical line. The stable charge states for each defect are labeled.

D. Form ation Energies in the O -rich Lim it

To address the characteristics of Co-doped samples grow n with OPM BE we nst consider conditions O-rich grow th conditions. Figure 2 shows the defect form ation energies versus Ferm ienergy in the O-rich limit, with the total Co concentration constrained to be 5%. In comparison to experiment this scenario has three main shortcom – ings: (1) the average magnetic moment is 1 $_{\rm B}$, signi – cantly smaller than the measured value^{3,4} of 1.26 $_{\rm B}$; (2) the Ferm i level is wellbelow midgap, whereas experimental measurements show the material to be n-type;^{1,4,14} (3) Co appears alm ost entirely as neutral substitutionals (oxidation state IV), whereas Co 2p photoem ission and XANES suggest that the conditions present during grow th of the samples are not O-rich.

E. Variation with O Chem ical Potential

To determ ine what grow th conditions give rise to the observed m agnetic and transport properties of C o-doped anatase sam ples, we study the consequences of varying the O chem ical potential away from its upper limit. In F ig. 3 we plot, versus the O chem ical potential, the follow ing quantities: concentration of of substitutional and interstitial C o; n and p carrier densities; average m agnetic m om ent per C o; percentage of C o in di erent oxidation states; and concentration of O vacancy-related defects (the concentration of interstitial T i is negligible throughout this range of O chem ical potential). For every



FIG.3: Variation, versus 0 chem ical potential, of (a) Co_{T i} concentration, (b) Co_{int} concentration, (c) carrier concentration, (d) average magnetic m on ent per Co, (e) percent of Co in various oxidation states, and (f) concentration of V₀ – related defects versus 0 chem ical potential. In panels (a) and (b) the concentration of each charge state of Co is indicated as well as the total concentration. In panel (f) only the concentration of Co_T iV₀ defects are shown, since the concentration of isolated 0 vacancies is m uch sm aller. Values of the 0 chem ical potential to the left of the dashed vertical line are those for which our theoretical results agree qualitatively with experiment (see text).

value of the O $\,$ chem ical potential, the total concentration of C $_{0}$ was constrained to 5% .

1. Cobalt concentration

For values of the 0 chem ical potential within 1.5 eV of the 0 -rich lim it, the substitutional site remains the

preferred Cosite. The situation is very di erent in the Opoor lim it. In this regime, interstitial Co (in the +1 and + 2 charge states) becom es energetically com petitive with substitutional Co, and hence the concentrations of substitutional and interstitial C o become comparable. This results from a subtle balance of the O and Co chemical potentials. As one decreases the 0 chem ical potential from its upper limit, the formation energies of substitutional dopants increases, since it costs m ore energy to replace T iw ith C o as one m oves tow ard the T i-rich lim it. Of course, as a function of the O chemical potential, the Co chem ical potential must also change, increasing monotonically to maintain the xed total Co concentration. At 1 eV below the O-rich limit, interstitial Co begins to play a role; the preference for the interstitial site increases m onotonically below this point, eventually accounting form ost of the total C o concentration in the 0-poor lim it.

2. Carrier densities

The defect concentrations shown in Fig. 3 were computed for a temperature of 873 K, as mentioned earlier. However, since transport, magnetom etry, and photoem ission measurements are generally performed at room temperature, we have used a more relevant temperature of 300 K to compute the carrier concentrations, magnetic moments, and oxidation-state fractions while keeping the total defect concentrations them selves frozen at their high-temperature values.

Figure 3 (c) shows the logarithm of the hole and electron carrier densities evaluated at 300 K as a function of the O chem ical potential. Near the O -rich lim it the carrier densities are nearly constant, since the Ferm i level m aintains a value of 0.8 eV relative to the VBM due to compensation by equalbut sm all num bers of substitutional C o in the 1 and +1 charge states. In this region the m aterial is very weakly p-type with a hole concentration $10^6/\text{cm}^3$ and will likely appear insulating in transport m easurem ents.

At 1 eV below the O -rich lim it, the appearance of interstitial C o leads to partial compensation of the C o substitutional defects. This compensation drives the Ferm i level towards the conduction-band edge, and leads to a marked increase in the electron concentration as the O chem ical potential is further reduced. The step-w ise behavior of the carrier density as the O chem ical potential is decreased results from the Ferm i level passing through donor levels due to interstitial C o. At the O -poor lim it, we nd n 10^{20} /cm³. Thus, we suggest that the experimentally observed n-type behavior results from the incom plete compensation of interstitial C o by substitutional C o, which facilitates the therm alexcitation of electrons from interstitial C o into the conduction band.

3. Magnetic moment

In Fig.3(d) we show the average magnetic moment per Co, de ned here as

$$\overline{\mathbf{M}} = \overset{\mathbf{X}}{\underset{\mathbf{D}}{\operatorname{p}}} \overset{\mathbf{q}}{\underset{\mathbf{Q}}{\operatorname{p}}} \overset{\mathbf{q}}{\underset{\mathbf{D}}{\operatorname{p}}} \overset{\mathbf{q}}{\underset{\mathbf{D}}{\operatorname{p}}} \overset{\mathbf{X}}{\underset{\mathbf{D}}{\operatorname{p}}} \overset{\mathbf{q}^{0}}{\underset{\mathbf{D}}{\operatorname{p}}} \overset{\mathbf{X}}{\underset{\mathbf{D}}{\operatorname{p}}} \overset{\mathbf{q}^{0}}{\underset{\mathbf{D}}{\operatorname{p}}} \overset{\mathbf{Q}}{\underset{\mathbf{D}}{\operatorname{p}}} \overset{\mathbf{Q}}{\underset{\mathbf{D}}{\operatorname{p}}} \overset{\mathbf{Q}}{\underset{\mathbf{D}}{\operatorname{p}}} \overset{\mathbf{Q}}{\underset{\mathbf{D}}{\operatorname{p}}} \overset{\mathbf{Q}}{\underset{\mathbf{D}}{\operatorname{p}}} \overset{\mathbf{Q}}{\underset{\mathbf{D}}{\operatorname{p}}} \overset{\mathbf{Q}}{\underset{\mathbf{D}}{\operatorname{p}}} \overset{\mathbf{Q}}{\underset{\mathbf{D}}{\operatorname{p}}} \overset{\mathbf{Q}}{\underset{\mathbf{Q}}{\operatorname{p}}} \overset{\mathbf{Q}}{\underset{\mathbf{D}}{\operatorname{p}}} \overset{\mathbf{Q}}{\underset{\mathbf{Q}}{\operatorname{p}}} \overset{\mathbf{Q}}{\underset{\mathbf{Q}}} \overset{\mathbf{Q}}} \overset{\mathbf{Q}}{\underset{\mathbf{Q}}{\operatorname{p}}} \overset{\mathbf{Q}}{\underset{\mathbf{Q}}}} \overset{\mathbf{$$

where M_{D}^{q} is the magnetic moment of a Co-related defect in charge state q. We assume a ferrom agnetic alignment of all the moments, and thus \overline{M} can be considered an upper bound for the measured average value of the moment per Co.

The average m om ent shows a non-m onotonic variation with 0 chem ical potential. In the 0 -rich region it is constant with a value of 1 $_{\rm B}$, because neutral substitutional C o is the dom inant defect. For interm ediate values of the 0 chem ical potential, $\overline{\rm M}$ is less than 1 $_{\rm B}$ due to the presence of substitutionals in the 1 charge state, which have zero m om ent. In the 0 -poor lim it the average m om ent per C o is larger than 1 $_{\rm B}$, due to the appearance of interstitial C o in the +1 charge state, which has a m om ent of 2 $_{\rm B}$. Hence, only in the 0 -poor lim it do we obtain a m om ent per C o larger than the C o²⁺ low -spin value of 1 $_{\rm B}$, and thus consistent with experiment.

4. Oxidation states

Figure 3 (e) shows the percentage of C o dopants in different oxidation states. In the O -rich lim it the oxidation state of C o is IV, since it occurs primarily as a neutral substitutional. This oxidation state dom inates until 1.5 eV below the O-rich lim it where oxidation state III, resulting from substitutionals in the 1 charge state, is brie y dom inant. Between 3 and 4 eV below the 0-rich lim it the predom inant oxidation state of Co is II, the same as that deduced from the 2p photoem ission and XANES results of Refs.4 and 14. In the O-poor lim it the oxidation state is primarily I, since the dom inant type of defect is interstitial C o in the + 1 charge state. A lthough this oxidation state has not been observed experim entally, com parison to photoem ission or XANES results on sam ples with known C o oxidation state of I has not been established.

5. O vacancies

For all therm odynam ically allowed chem ical potentials, the concentration of isolated O vacancies is negligible, as well as that of Co_T $_{i}V_{O}$ com plexes; their concentrations are shown in Fig. 3 (f) to be never above 10 5 %. These low concentrations result from the fact that the form ation energies of these two defects are much higher than the therm al energy $k_{B}T = 60 \text{ meV}$; this is clear from Fig. 2, where the form ation energy of both isolated V₀ and Co_{T i}V₀ com plexes is greater than 2 eV for any value

of the Ferm i level. Thus O vacancies, either isolated or in complexes with substitutional Co, will play no signi cant role in determ ining the carrier concentration in Co-doped sam ples.

W e note that the form ation energies of O vacancies in Fig. 2 and the deduced donor level positions in the band gap are incompatible with the interpretation of the observed n-type conductivity of pure T iO $_2$ sam ples.¹⁰ E ven in the O-poor limit, the LDA does not lead to a carrier density with the observed value 10^{18} /cm³, nor does it give the same tem perature dependence of the carrier concentration, as the energy for activation is quite di erent: 200 m eV (the position of the highest 0 vacancy donor level below the conduction band edge) in the LDA versus 4.2 m eV in the results of R ef. 10. W e do not have a de nitive resolution to this apparent disagreem ent; we have checked, however, that if we adjust the 0 vacancy form ation energies to reproduce the experim entally observed carrier density and tem perature dependence in undoped samples, the conclusions of this work are unchanged.

R egarding the experimental interpretation that O vacancies are also the source of n-type carriers in C o doped samples,^{3,4} we note that the observed average moment per C o of 1.26 $_{\rm B}$ can only be reproduced if some fraction of C o interstitials in the + 2 charge state are present, as only these defects have a moment larger than 1 $_{\rm B}$. Neither substitutional nor interstitial C o has any signic cant orbitalm om ent²⁶ so that the observed m agnetic moment per C o can only result from the statistical distribution of C o moments in interstitial (2 $_{\rm B}$) and substitutional (1 $_{\rm B}$) sites. In such a situation the Ferm i level and carrier concentration are determined solely by the C o dopants.

6. Conclusion

C onsidering these trends in the n-type carrier density, average magnetic moment per Co, and oxidation state of Co, we suggest the actual conditions of growth of Co-doped TiO₂ anatase are O-poor, corresponding to O chem ical potentials between 3.8 and 4.6 eV below the O-rich limit (values of the O chem ical potential to the left of the dashed vertical line in Fig. 3). Under these type of conditions we obtain qualitatively and quantitatively good agreem ent with experimental observations.

V. SUMMARY

In summary, we have examined the role of native defects and Co dopants in TiD_2 anatase over a range of chem ical potentials corresponding to di erent grow th conditions. Under O -rich grow th conditions we nd that Co dopants will be form ed primarily in neutral substitutional form corresponding to oxidation state IV, an average magnetic moment of 1 $_{\rm B}$ and insulating electrical character. These results are in condict with the exper-

im entally observed behavior of Co-doped samples and suggest that the growth conditions are more likely to be O-poor. O-poor conditions lead to roughly equal concentrations of substitutional and interstitial Co, n-type behavior resulting from thermal excitation of electrons from interstitialCo into the conduction band, and an average m agnetic mom ent per Co in good agreem ent with experiment.

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